



STT2PF60L

P-CHANNEL 60V - 0.20 Ω - 2A - SOT-23-6L
STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STT2PF60L	60V	< 0.25 Ω	2A

- Standard outline for easy automated surface mount assembly
- Low threshold drive

Description

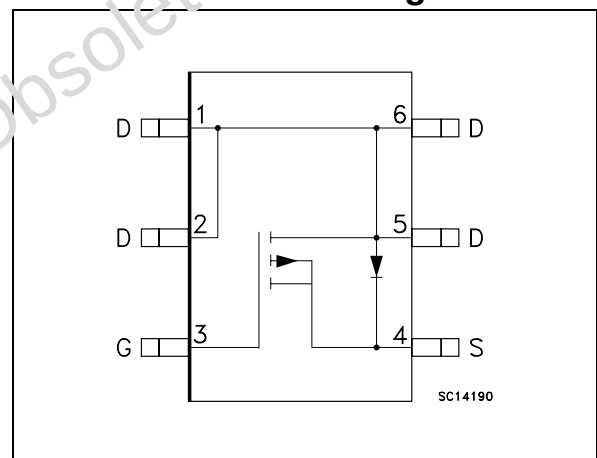
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- DC motor drive
- DC-DC converters
- Battery management in nomadic equipment
- Power management in portable/desktop PCs
- Cellular



Internal schematic diagram



Order codes

Sales Type	Marking	Package	Packaging
STT2PF60L	STP6	SOT23-6L	Tape & Reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS} = 0$)	60	V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20k\Omega$)	60	V
V_{GS}	Gate-Source Voltage	± 15	V
I_D	Drain Current (continuous) at $T_C = 25^\circ C$	2	A
I_D	Drain Current (continuous) at $T_C = 100^\circ C$	1.3	A
$I_{DM}^{(1)}$	Drain Current (pulsed)	8	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ C$	1.6	W

1. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJ-amb}^{(1)}$	Thermal resistance junction-case Max	78	$^\circ C/W$
T_j	Maximum operating junction temperature	150	$^\circ C$
T_{stg}	Storage temperature	-55 to 150	$^\circ C$

1. Mounted on a 1 in² pad of 2 oz Cu in FR-4 board for $t < 10\text{sec}$

Note: For the P-Channel MOSFET actual polarity of voltage and current has to be reversed

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$, $V_{DS} = \text{Max Rating}$, $T_c=125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate Body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 15\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1			V
$R_{DS(on)}$	Static Drain-Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 1\text{A}$ $V_{GS} = 4.5\text{V}$, $I_D = 1\text{A}$		0.20 0.24	0.25 0.30	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 1\text{A}$		3		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		313 67 25		pF pF pF
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 30\text{V}$, $I_D = 24\text{A}$ $V_{GS} = 10\text{V}$ (see Figure 14)		5 0.5 2.2	7	nC nC nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Note: For the P-Channel MOSFET actual polarity of voltage and current has to be reversed

Table 5. Switching times

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD}=30V$, $I_D=1A$, $R_G=4.7\Omega$, $V_{GS}=4.5V$ (see Figure 13)		44 34		ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD}=30V$, $I_D=1A$, $R_G=4.7\Omega$, $V_{GS}=4.5V$ (see Figure 13)		42 15		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain Current Source-drain Current (pulsed)				2 8	A A
$V_{SD}^{(2)}$	Forward on Voltage	$I_{SD}=2A$, $V_{GS}=0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD}=2A$, $di/dt = 100A/\mu s$, $V_{DD}=30V$, $T_j=150^\circ C$		38 36.3 2.5		ns nC A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Note: For the P-Channel MOSFET actual polarity of voltage and current has to be reversed

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

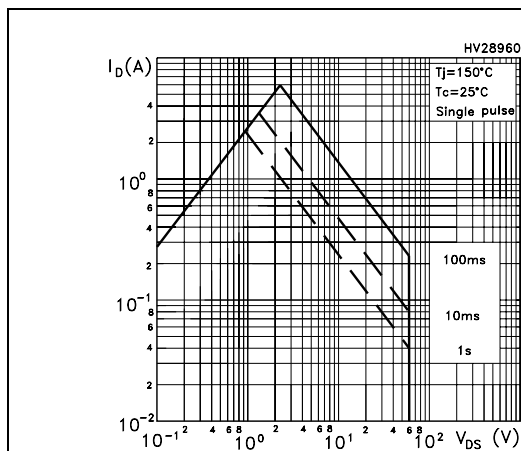


Figure 2. Thermal impedance

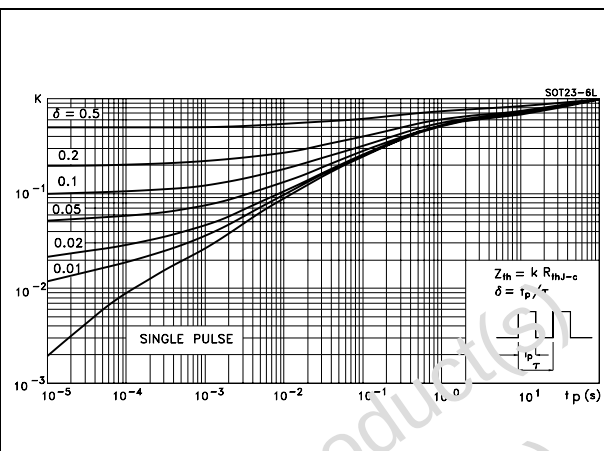


Figure 3. Output characteristics

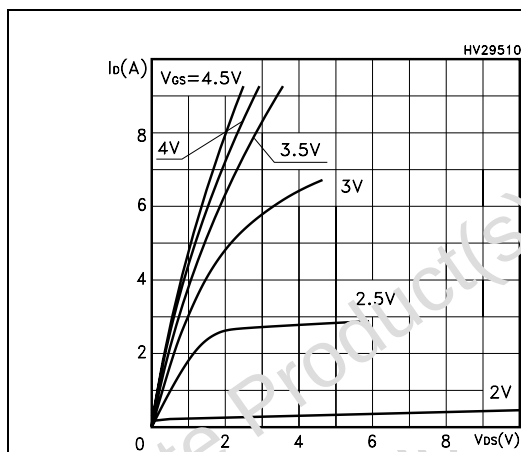


Figure 4. Transfer characteristics

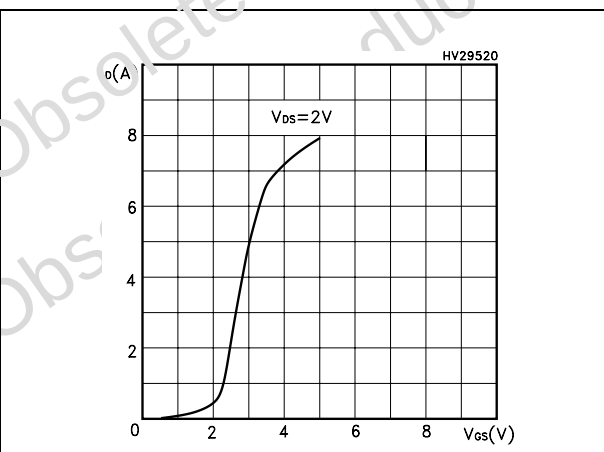


Figure 5. Transconductance

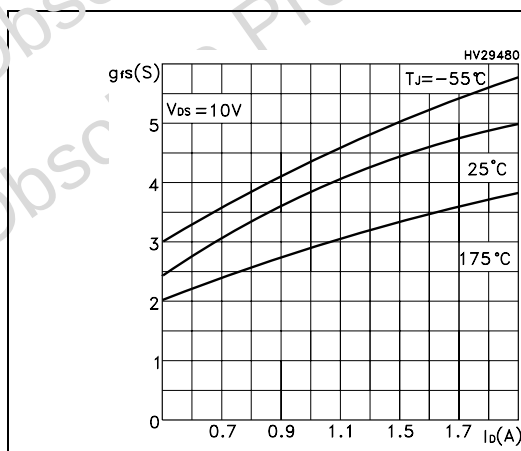


Figure 6. Static drain-source on resistance

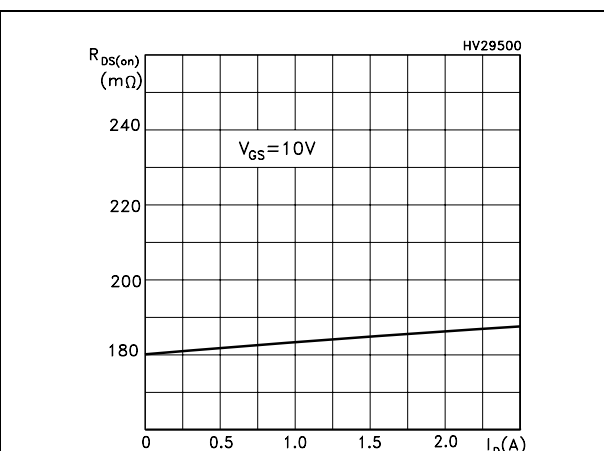


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

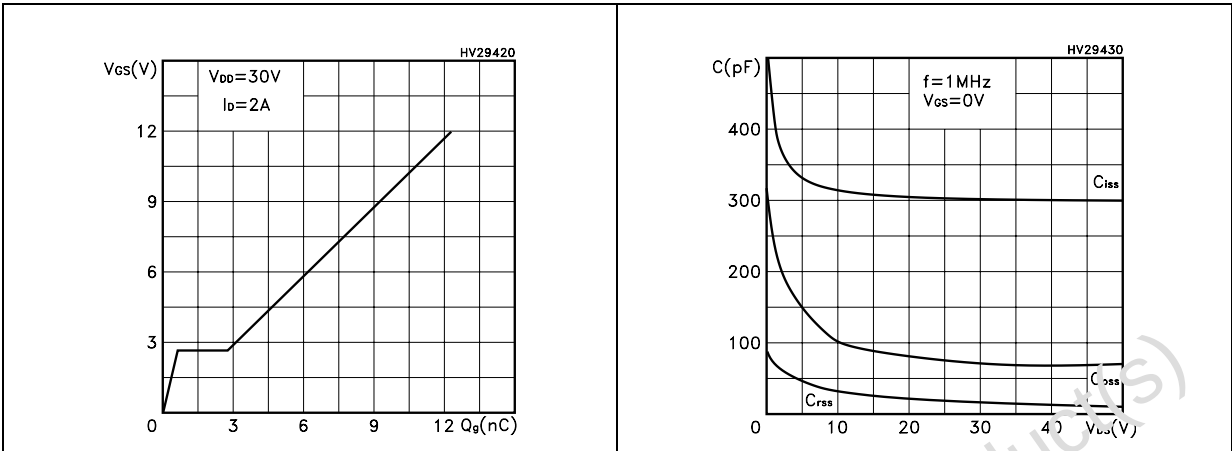


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on-resistance vs temperature

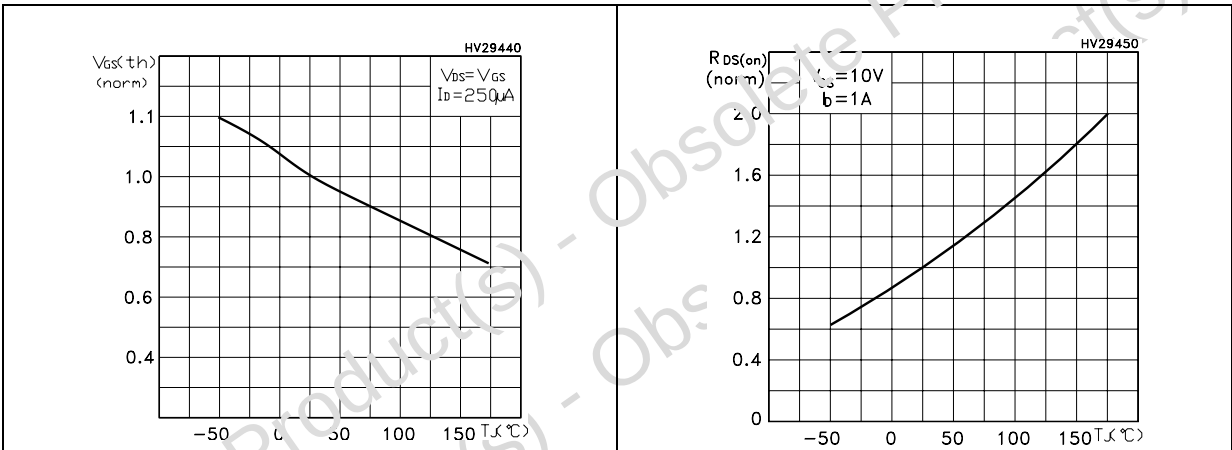
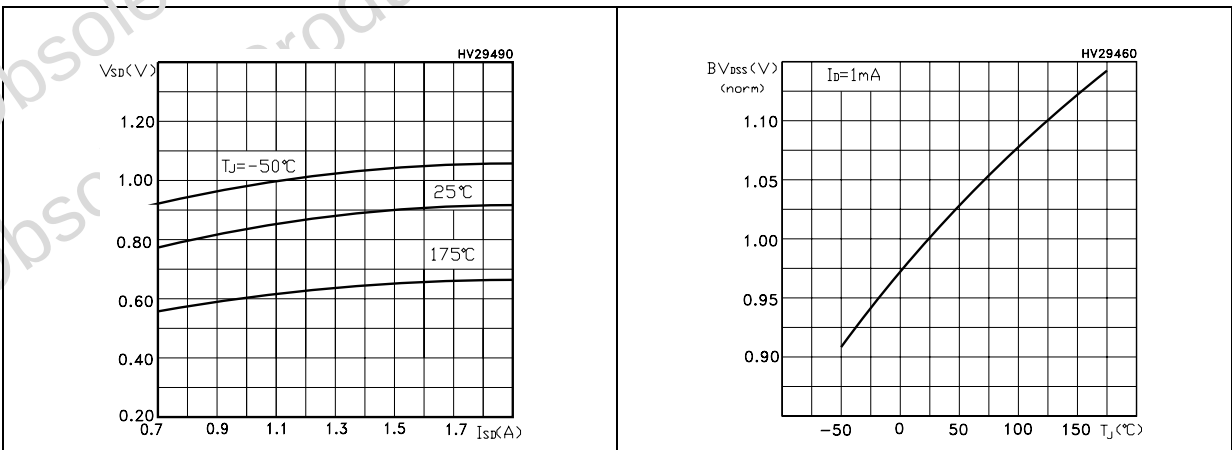


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized $B_{V_{DS}}$ vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

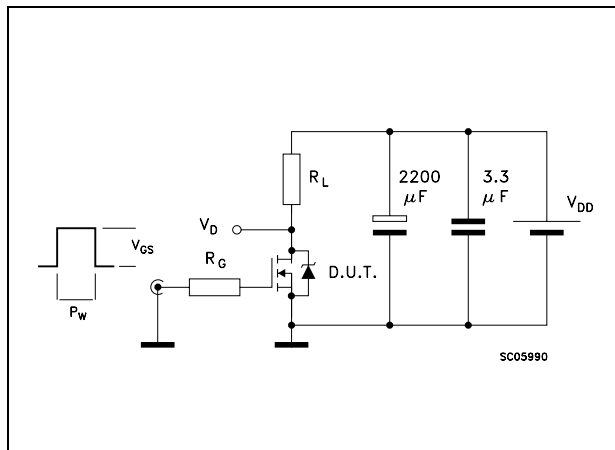


Figure 14. Gate charge test circuit

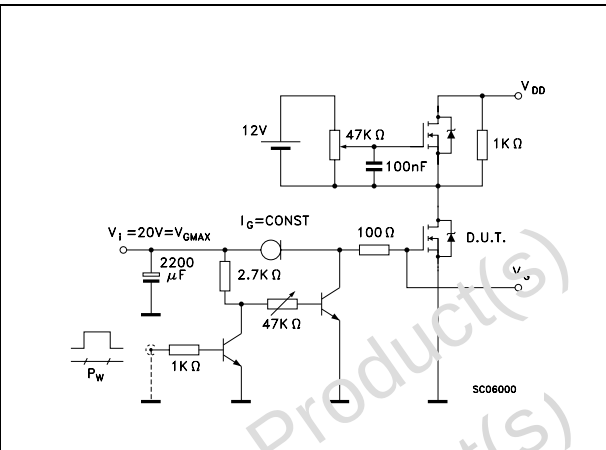


Figure 15. Test circuit for inductive load switching and diode recovery times

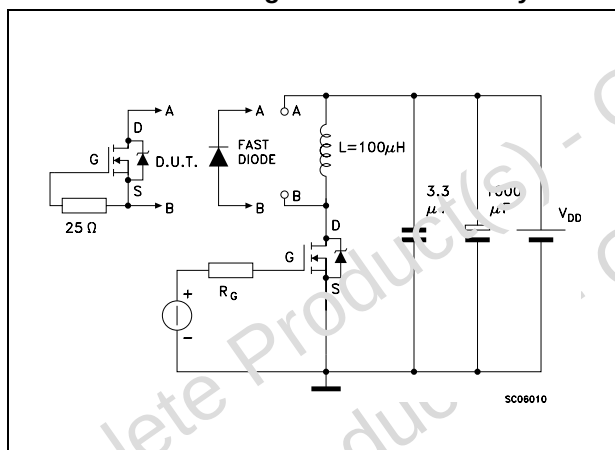


Figure 16. Unclamped Inductive load test circuit

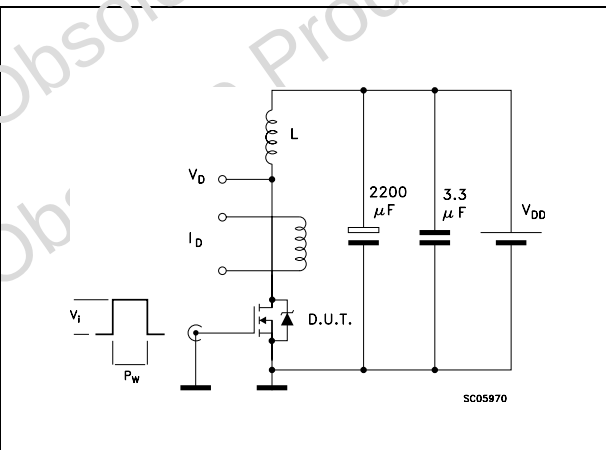
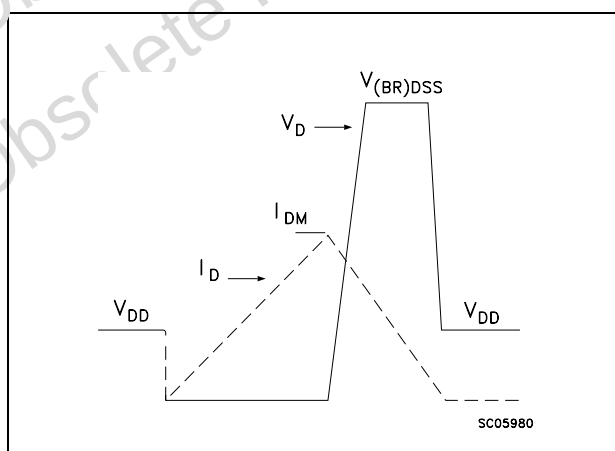


Figure 17. Unclamped inductive waveform



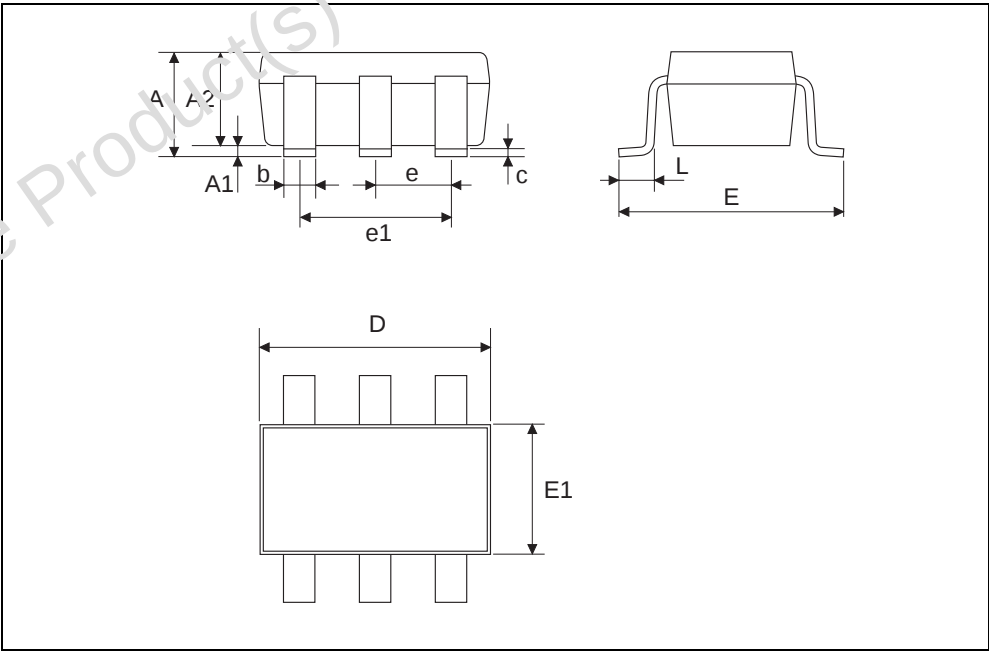
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)
Obsolete Product(s) - Obsolete Product(s)

TSOP-6 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	0.035		0.057
A1	0.00		0.15	0.000		0.006
A2	0.90		1.30	0.035		0.051
b	0.25		0.50	0.010		0.020
C	0.09		0.20	0.004		0.008
D	2.80		3.10	0.110		0.122
E	2.60		3.00	0.102		0.118
E1	1.50		1.75	0.059		0.069
L	0.35		0.55	0.014		0.022
e		0.95			0.037	
e1		1.90			0.075	



5 Revision history

Table 7. Document revision history

Date	Revision	Changes
07-May-2002	1	Initial release.
19-Apr-2003	2	Preliminary version
22-Dec-2005	3	Final version

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.